

REMARKS

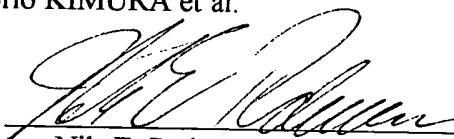
The present Preliminary Amendment is submitted to delete the multiple dependency of the claims, thereby placing such claims in condition for examination and reducing the required PTO filing fee.

Attached hereto is a marked-up version of the changes made to the claim by the current Preliminary Amendment. The attached page is captioned "**Version With Markings to Show Changes Made**".

Respectfully submitted,

Norio KIMURA et al.

By



Nils E. Pedersen

Registration No. 33,145

Attorney for Applicants

NEP/krl
Washington, D.C. 20006-1021
Telephone (202) 721-8200
Facsimile (202) 721-8250
May 25, 2001

THE COMMISSIONER IS AUTHORIZED
TO CHARGE ANY DEFICIENCY IN THE
FEES FOR THIS PAPER TO DEPOSIT
ACCOUNT NO. 23-0975

Revision with Markings to
Show Changes Made

detected by said film thickness detecting means.

3. A substrate polishing apparatus according to claim 1 [or 2], further comprising dressing means for dressing said polishing surface of said polishing table or cleaning means for cleaning said polishing surface of said polishing table, and wherein said control mechanism controls said dressing means or said cleaning means between the polishing processes to effect the dressing or the cleaning of said polishing surface of said polishing table.

4. A substrate polishing method in which a semiconductor substrate held by a top ring is pressed against a polishing surface of a polishing table and a surface to be polished of the semiconductor substrate is polished by a relative movement between the semiconductor substrate and said polishing surface, wherein:

the semiconductor substrate is polished on the same polishing table through plural polishing processes while changing an pressing force for pressing the semiconductor substrate and the number of revolutions of said top ring and/or said polishing table.

5. A substrate polishing method according to claim 4, wherein, when said plural polishing processes are performed, the polishing is effected while adding polishing liquid and/or reagent liquid having having pH at the same side as pH 7.

6. A substrate polishing method according to claim 4, wherein, when said plural polishing processes are performed, the polishing is effected by using same abrasive